

Complementary MOSFET

ELM34604AA-N

General Description

ELM34604AA-N uses advanced trench technology to provide excellent $R_{ds(on)}$ and low gate charge.

Features

- | | |
|--|--|
| N-channel | P-channel |
| • $V_{ds}=40V$ | $V_{ds}=-40V$ |
| • $I_d=7A$ | $I_d=-5A$ |
| • $R_{ds(on)} < 28m\Omega (V_{gs}=10V)$ | $R_{ds(on)} < 65m\Omega (V_{gs}=-10V)$ |
| • $R_{ds(on)} < 42m\Omega (V_{gs}=4.5V)$ | $R_{ds(on)} < 105m\Omega (V_{gs}=-4.5V)$ |

Maximum Absolute Ratings

Parameter	Symbol	N-ch (Max.)	P-ch (Max.)	Unit	Note
Drain-source voltage	V_{ds}	40	-40	V	
Gate-source voltage	V_{gs}	± 20	± 20	V	
Continuous drain current	I_d	$T_a=25^\circ C$	7	-6	A
		$T_a=70^\circ C$	6	-5	
Pulsed drain current	I_{dm}	20	-20	A	1
Power dissipation	P_d	$T_a=25^\circ C$	2.0	2.0	W
		$T_a=70^\circ C$	1.3	1.3	
Junction and storage temperature range	T_j, T_{stg}	-55 to 150	-55 to 150	$^\circ C$	

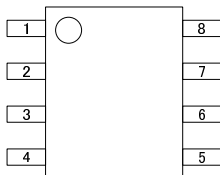
Thermal Characteristics

Parameter	Symbol	Device	Typ.	Max.	Unit	Note
Maximum junction-to-ambient	$R\theta_{ja}$	N-ch		62.5	$^\circ C/W$	
Maximum junction-to-ambient	$R\theta_{ja}$	P-ch		62.5	$^\circ C/W$	

- Pulse width limited by maximum junction temperature.
- Duty cycle $\leq 1\%$.

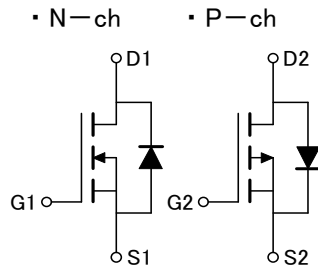
Pin Configuration

SOP-8 (TOP VIEW)



Pin No.	Pin name
1	SOURCE1
2	GATE1
3	SOURCE2
4	GATE2
5	DRAIN2
6	DRAIN2
7	DRAIN1
8	DRAIN1

Circuit



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■ Electrical Characteristics (N-ch)

T_a=25°C

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	Note	
STATIC PARAMETERS								
Drain-source breakdown voltage	BV _{dss}	I _d =250 μA, V _{gs} =0V	40			V		
Zero gate voltage drain current	I _{dss}	V _{ds} =32V, V _{gs} =0V			1	μA		
		V _{ds} =30V, V _{gs} =0V, T _j =55°C			10			
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±20V			±100	nA		
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =250 μA	1.0	1.5	2.5	V		
On state drain current	I _{d(on)}	V _{gs} =10V, V _{ds} =5V	20			A	1	
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =10V, I _d =7A		21	28	mΩ	1	
		V _{gs} =4.5V, I _d =6A		30	42			
Forward transconductance	G _{fs}	V _{ds} =10V, I _d =7A		19		S	1	
Diode forward voltage	V _{sd}	I _f =I _s , V _{gs} =0V			1	V	1	
Max.body-diode continuous current	I _s				1.3	A		
Pulsed current	I _{sm}				2.6	A	3	
DYNAMIC PARAMETERS								
Input capacitance	C _{iss}	V _{gs} =0V, V _{ds} =10V, f=1MHz		790		pF		
Output capacitance	C _{oss}				175		pF	
Reverse transfer capacitance	C _{rss}				65		pF	
SWITCHING PARAMETERS								
Total gate charge	Q _g	V _{gs} =10V, V _{ds} =20V, I _d =7A		16.0		nC	2	
Gate-source charge	Q _{gs}			2.5		nC	2	
Gate-drain charge	Q _{gd}			2.1		nC	2	
Turn-on delay time	t _{d(on)}	V _{gs} =10V, V _{ds} =20V, I _d ≈ 1A R _{gen} =6 Ω		2.2	4.4	ns	2	
Turn-on rise time	t _r			7.5	15.0	ns	2	
Turn-off delay time	t _{d(off)}			11.8	21.3	ns	2	
Turn-off fall time	t _f			3.7	7.4	ns	2	

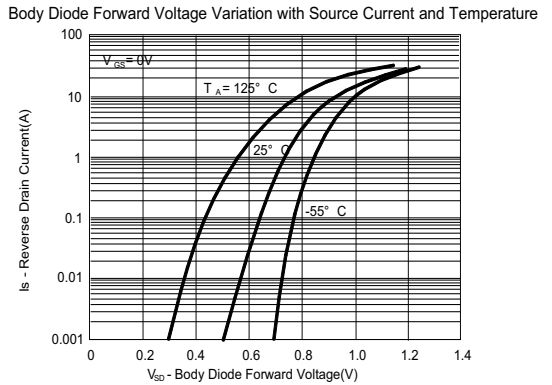
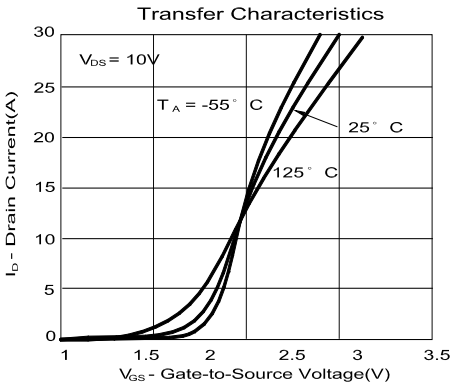
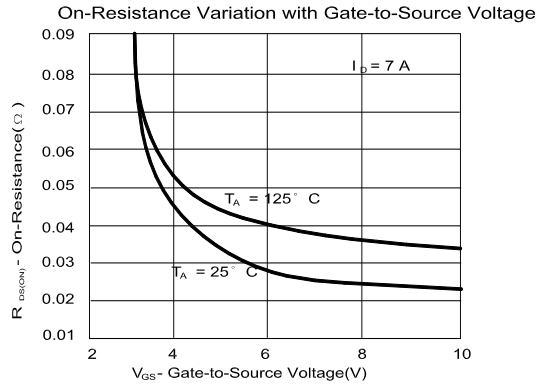
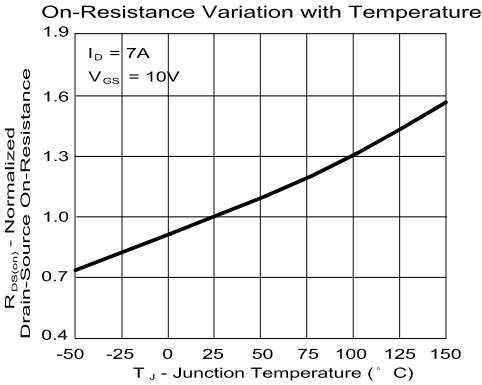
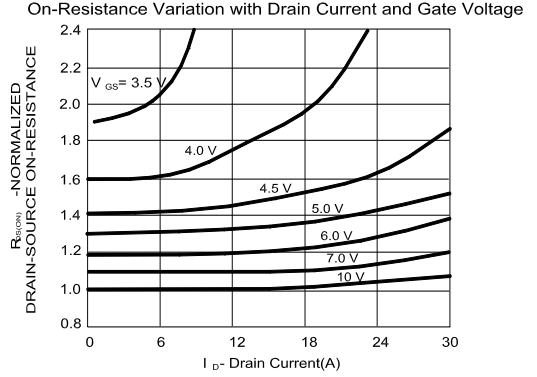
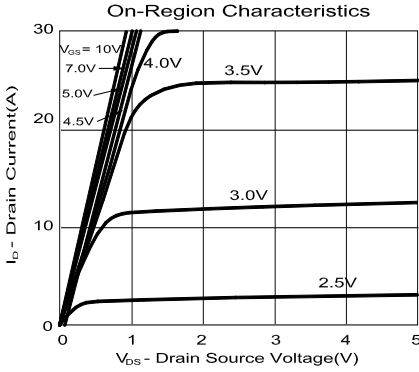
NOTE :

1. Pulse test : Pulse width ≤ 300 μsec, duty cycle ≤ 2%.
2. Independent of operating temperature.
3. Pulse width limited by maximum junction temperature.

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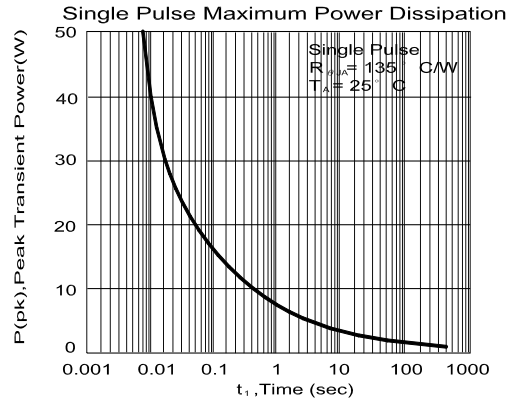
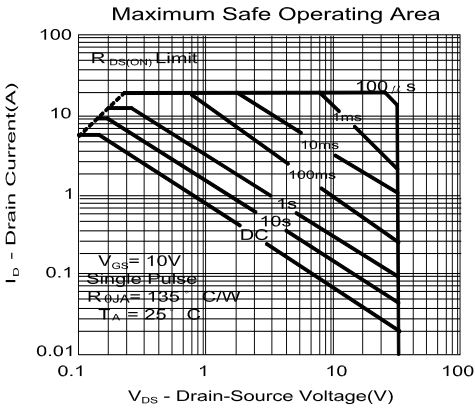
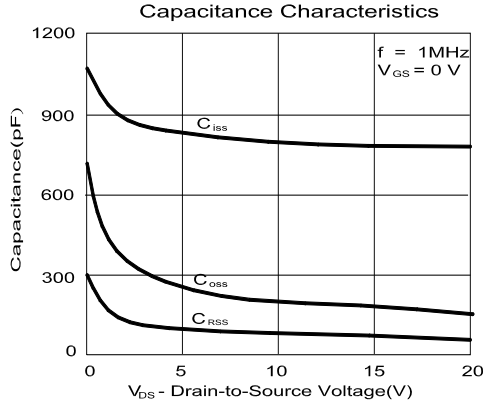
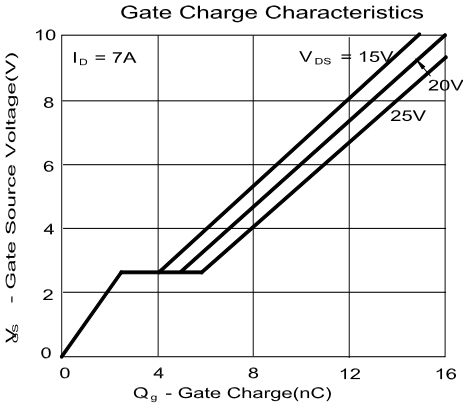
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Typical Electrical and Thermal Characteristics (N-ch)



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Complementary MOSFET

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■ Electrical Characteristics (P-ch)

T_a=25°C

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit	Note
STATIC PARAMETERS							
Drain-source breakdown voltage	BV _{dss}	I _d =-250μA, V _{gs} =0V	-40			V	
Zero gate voltage drain current	I _{dss}	V _{ds} =-32V, V _{gs} =0V			-1	μA	
		V _{ds} =-30V, V _{gs} =0V, T _j =55°C			-10		
Gate-body leakage current	I _{gss}	V _{ds} =0V, V _{gs} =±20V			±100	nA	
Gate threshold voltage	V _{gs(th)}	V _{ds} =V _{gs} , I _d =-250μA	-1.0	-1.5	-2.5	V	
On state drain current	I _{d(on)}	V _{gs} =-10V, V _{ds} =-5V	-20			A	1
Static drain-source on-resistance	R _{ds(on)}	V _{gs} =-10V, I _d =-5A		50	65	mΩ	1
		V _{gs} =-4.5V, I _d =-4A		80	105		
Forward transconductance	G _{fs}	V _{ds} =-10V, I _d =-5A		11		S	1
Diode forward voltage	V _{sd}	I _f =I _s , V _{gs} =0V			-1	V	1
Max.body-diode continuous current	I _s				-1.3	A	
Pulsed current	I _{sm}				-2.6	A	3
DYNAMIC PARAMETERS							
Input capacitance	C _{iss}	V _{gs} =0V, V _{ds} =-10V, f=1MHz		690		pF	
Output capacitance	C _{oss}			310		pF	
Reverse transfer capacitance	C _{rss}			75		pF	
SWITCHING PARAMETERS							
Total gate charge	Q _g	V _{gs} =-10V, V _{ds} =-20V I _d =-5A		14.0		nC	2
Gate-source charge	Q _{gs}			2.2		nC	2
Gate-drain charge	Q _{gd}			1.9		nC	2
Turn-on delay time	t _{d(on)}	V _{gs} =-10V, V _{ds} =-20V I _d ≈-1A, R _l =1Ω, R _{gen} =6Ω		6.7	13.4	ns	2
Turn-on rise time	t _r			9.7	19.4	ns	2
Turn-off delay time	t _{d(off)}			19.8	35.6	ns	2
Turn-off fall time	t _f			12.3	22.2	ns	2

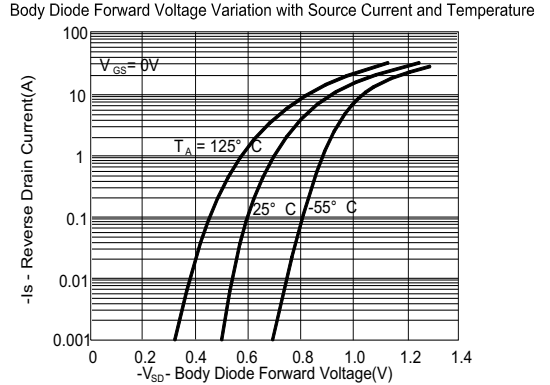
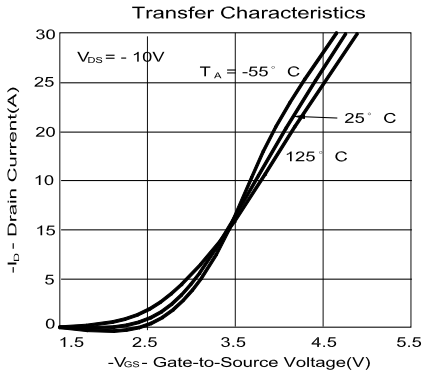
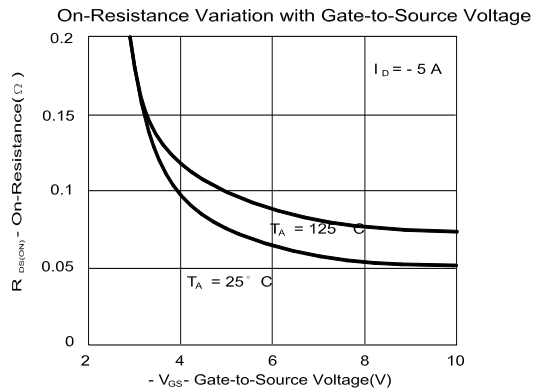
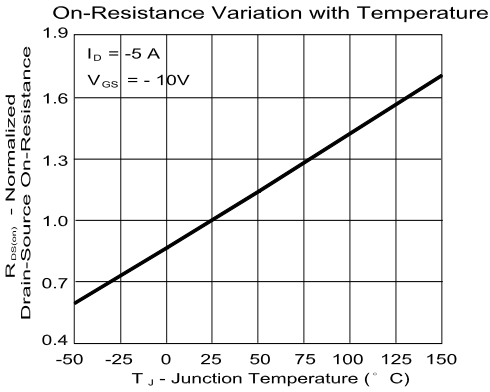
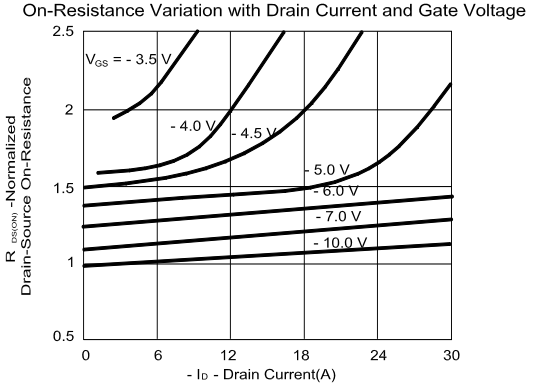
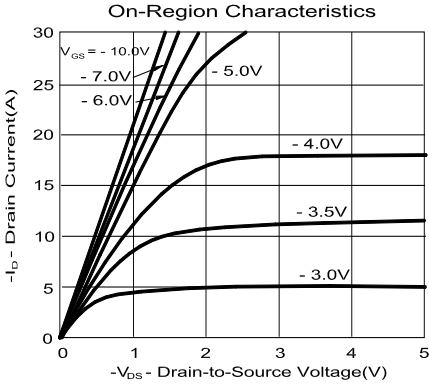
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